

50A, 1200V Hyperfast Diode

The RHRG50120 is a hyperfast diode with soft recovery characteristics ($t_{rr} < 85ns$). It has half the recovery time of ultrafast diodes and is of silicon nitride passivated ion-implanted epitaxial planar construction.

This device is intended for use as a freewheeling/clamping diode and rectifier in a variety of switching power supplies and other power switching applications. Its low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits, thus reducing power loss in the switching transistors.

Formerly developmental type TA49100.

Ordering Information

PART NUMBER	PACKAGE	BRAND
RHRG50120	TO-247	RHRG50120

NOTE: When ordering, use the entire part number.

Symbol



Features

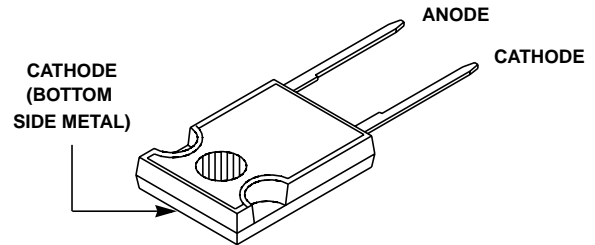
- Hyperfast with Soft Recovery <85ns
- Operating Temperature 175°C
- Reverse Voltage 1200V
- Avalanche Energy Rated
- Planar Construction

Applications

- Switching Power Supplies
- Power Switching Circuits
- General Purpose

Packaging

JEDEC STYLE TO-247



Absolute Maximum Ratings $T_C = 25^\circ C$, Unless Otherwise Specified

	RHRG50120	UNITS
Peak Repetitive Reverse Voltage	1200	V
Working Peak Reverse Voltage	1200	V
DC Blocking Voltage	1200	V
Average Rectified Forward Current $T_C = 50^\circ C$	50	A
Repetitive Peak Surge Current Square Wave, 20kHz	100	A
Nonrepetitive Peak Surge Current Halfwave, 1 Phase, 60Hz	500	A
Maximum Power Dissipation	150	W
Avalanche Energy (See Figures 10 and 11)	50	mJ
Operating and Storage Temperature	-65 to 175	°C

Electrical Specifications $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
V_F	$I_F = 50\text{A}$	-	-	3.2	V
	$I_F = 50\text{A}, T_C = 150^\circ\text{C}$	-	-	2.6	V
I_R	$V_R = 1200\text{V}$	-	-	500	μA
	$V_R = 1200\text{V}, T_C = 150^\circ\text{C}$	-	-	1.0	mA
t_{rr}	$I_F = 1\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}$	-	-	85	ns
	$I_F = 50\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}$	-	-	100	ns
t_a	$I_F = 50\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}$	-	50	-	ns
t_b	$I_F = 50\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}$	-	35	-	ns
Q_{RR}	$I_F = 50\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}$	-	400	-	nC
C_J	$V_R = 10\text{V}, I_F = 0\text{A}$	-	150	-	pF
$R_{\theta JC}$		-	-	1.0	$^\circ\text{C}/\text{W}$

DEFINITIONS

V_F = Instantaneous forward voltage (pw = 300 μs , D = 2%).

I_R = Instantaneous reverse current.

t_{rr} = Re